a tirst cladding layer having said first conductivity type, said first cladding layer being formed on said buffer layer epitaxially;

an active layer formed epitaxially on said first cladding layer;

a second cladding layer having a second, opposite conductivity type, said second cladding layer being formed on said active layer epitaxially;

a first electrode provided so as to inject first-type carriers having a first polarity into said second cladding layer; and

a second electrode provided on a bottom surface of said substrate so as to inject second-type carriers having a second polarity,

said buffer layer containing said first type carriers with a concentration level in the range from 3 x 10^{18} cm⁻³ to 1 x 10^{20} cm⁻³ and said compositional parameter x larger than 0 but smaller than 0.4 (0 < x < 0.4).